

LPV531

Programmable CMOS Input, Rail-to-Rail Output Operational Amplifier

General Description

The LPV531 is an extremely versatile operational amplifier. A single external resistor gives the system designer the ability to program the quiescent current, gain bandwidth product and output short circuit current. This innovative feature gives the system designer a method to dynamically optimize the performance of the op amp to meet the system design requirements.

The LPV531 can be tailored to a wide variety of applications, it offers the system designer the ability to trade off supply current for bandwidth. The LPV531 is capable of operating from 73 kHz, consuming only 5 μ A, to as fast as 4.6 MHz, consuming only 425 μ A. The input offset voltage is relatively independent and therefore is not effected by the chosen power level.

Utilizing a CMOS input stage, the LPV531 achieves an input bias current of 50 fA and a common mode input voltage which extends from the negative rail to within 1.2V of the positive supply. The LPV531's rail-to-rail class AB output stage enables this op amp to offer maximum dynamic range at low supply voltage.

Available in the space saving 6-pin SOT23 package, the LPV531 is ideal for use in handheld electronics and portable applications. The LPV531 is manufactured using National's advanced VIP50 process.

A fixed supply current/gain bandwidth is available upon request.

Features

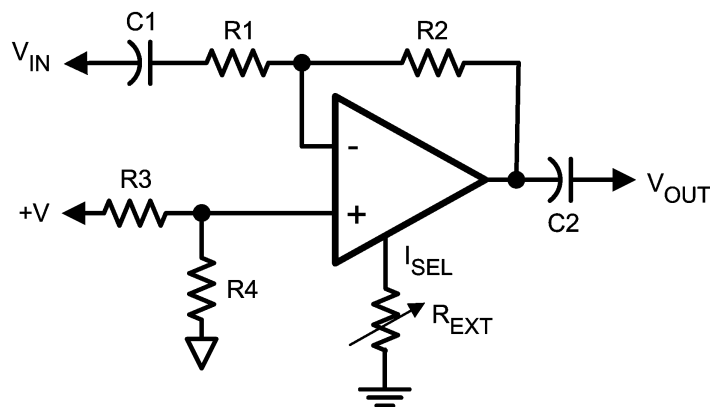
(Typical 5V supply, unless otherwise noted)

■ Supply voltage	2.7V to 5.5V
■ Supply current	
— Low power mode	5 μ A
— Mid power mode	42 μ A
— Full power mode	425 μ A
■ Input common mode voltage range	-0.3V to 3.8V
■ CMRR	95 dB
■ Output voltage swing	Rail-to-rail
■ Input offset voltage	1 mV
■ Bandwidth	
— Low power mode	73 kHz
— Mid power mode	625 kHz
— Full power mode	4.6 MHz

Applications

- AC coupled circuits
- Portable instrumentation
- Active filters

Typical Application



AC Coupled Application

20132335

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

ESD Tolerance (Note 2)	
Human Body Model	2000V
Machine Model	200V
V _{IN} Differential	±2V
Supply Voltage (V ⁺ - V ⁻)	6V
Storage Temperature Range	-65°C to +150°C
Junction Temperature (Note 5)	+150°C

Soldering Information

Infrared or Convection (20 sec)	235°C
Wave Soldering Lead Temp. (10 sec)	260°C

Operating Ratings (Note 1)

Operating Temperature Range	-40°C to +85°C
Supply Voltage (V ⁺ - V ⁻)	2.7V to 5.5V
Package Thermal Resistance (θ _{JA}) (Note 4)	171°C/W
6-Pin SOT23	

5V Full Power Mode Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for T_J = 25°C, V⁺ = 5V, V⁻ = 0V, V_{CM} = V_O = V⁺/2, I_{SEL} pin connected to V⁻, R_L = 100 kΩ. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units	
V _{OS}	Input Offset Voltage			±1	±4.5 ±5	mV	
ΔV _{OS}	Input Offset Voltage Difference	V _{OS} in Full Power Mode - V _{OS} in Low Power Mode		±0.1	±2	mV	
TC V _{OS}	Input Offset Average Drift	(Note 8)		±2		μV/C	
I _B	Input Bias Current			50		fA	
CMRR	Common Mode Rejection Ratio	V _{CM} Stepped from 0V to 3.5V	72 68	95		dB	
PSRR	Power Supply Rejection Ratio	V ⁺ = 2.7V to 5.5V V _{CM} = 1V	74 70	90		dB	
CMVR	Input Common Mode Voltage Range	CMRR ≥ 50 dB	-0.3		3.8	V	
A _{VOL}	Large Signal Voltage Gain	V _O = 0.5V to 4.5V R _L = 1 kΩ to V ⁺ /2	87 84	96		dB	
		V _O = 0.5V to 4.5V R _L = 10 kΩ to V ⁺ /2	104 100	114			
		V _O = 0.5V to 4.5V R _L = 100 kΩ, to V ⁺ /2	108 104	128			
V _O	Output Swing High	R _L = 1 kΩ to V ⁺ /2	180 195	120		mV from V ⁺	
		R _L = 10 kΩ to V ⁺ /2	80 85	55			
		R _L = 100 kΩ to V ⁺ /2	50 60	30			
	Output Swing Low	R _L = 1 kΩ to V ⁺ /2			160	210 230	mV
		R _L = 10 kΩ to V ⁺ /2			105	120 135	
		R _L = 100 kΩ to V ⁺ /2			95	120 135	
I _{SC}	Output Short Circuit Current	Sourcing, V _O = 2.5V V _{ID} = 100 mV		-15	-8 -3	mA	
		Sinking, V _O = 2.5V V _{ID} = -100 mV	13 10	24			
I _S	Supply Current			425	530 650	μA	

5V Full Power Mode Electrical Characteristics (Continued)

Unless otherwise specified, all limits are guaranteed for $T_J = 25^\circ\text{C}$, $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{\text{CM}} = V_O = V^+/2$, I_{SEL} pin connected to V^- , $R_L = 100\text{ k}\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
SR	Slew Rate (Note 7)	$A_V = +1$, $V_{\text{IN}} = 0.5\text{V to } 3.5\text{V}$ $C_L = 15\text{ pF}$	1.55 1	2.5		V/ μs
GBW	Gain Bandwidth Product	$C_L = 20\text{ pF}$		4.6		MHz
e_n	Input-Referred Voltage Noise	$f = 100\text{ kHz}$		20		nV/ $\sqrt{\text{Hz}}$
		$f = 1\text{ kHz}$		25		
i_n	Input-Referred Current Noise	$f = 1\text{ kHz}$		0.006		pA/ $\sqrt{\text{Hz}}$

5V Mid Power Mode Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for $T_J = 25^\circ\text{C}$, $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{\text{CM}} = V_O = V^+/2$, I_{SEL} pin connected to V^- through $100\text{ k}\Omega$ resistor, $R_L = 100\text{ k}\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
V_{OS}	Input Offset Voltage			± 1	± 4.5 ± 5	mV
ΔV_{OS}	Input Offset Voltage Difference	V_{OS} in Full Power Mode – V_{OS} in Low Power Mode		± 0.1	± 2	mV
TC V_{OS}	Input Offset Average Drift	(Note 8)		± 2		$\mu\text{V}/\text{C}$
I_B	Input Bias Current			50		fA
CMRR	Common Mode Rejection Ratio	V_{CM} Stepped from $0\text{V to } 3.5\text{V}$	72 68	92		dB
PSRR	Power Supply Rejection Ratio	$V^+ = 2.7\text{V to } 5.5\text{V}$	72 68	88		dB
CMVR	Input Common Mode Voltage Range	CMRR $\geq 50\text{ dB}$	-0.3		3.8	V
A_{VOL}	Large Signal Voltage Gain	$V_O = 0.5\text{V to } 4.5\text{V}$ $R_L = 10\text{ k}\Omega$	86 82	96		dB
		$V_O = 0.5\text{V to } 4.5\text{V}$ $R_L = 100\text{ k}\Omega$	100 98	114		
V_O	Output Swing High	$R_L = 10\text{ k}\Omega$ to $V^+/2$		115	160 175	mV from V^+
		$R_L = 100\text{ k}\Omega$ to $V^+/2$		65	110 120	
	Output Swing Low	$R_L = 10\text{ k}\Omega$ to $V^+/2$		150	165 180	mV
		$R_L = 100\text{ k}\Omega$ to $V^+/2$		105	120 135	
I_{SC}	Output Short Circuit Current	Sourcing, $V_O = 2.5\text{V}$ $V_{\text{ID}} = 100\text{ mV}$		-4	-1.5 -1	mA
		Sinking, $V_O = 2.5\text{V}$ $V_{\text{ID}} = -100\text{ mV}$	1.5 1	4		
I_S	Supply Current			42	55 62	μA
SR	Slew Rate (Note 7)	$A_V = +1$, $V_{\text{IN}} = 0.5\text{V to } 3.5\text{V}$	180 100	250		V/ms
GBW	Gain Bandwidth Product	$C_L = 20\text{ pF}$		625		kHz
e_n	Input-Referred Voltage Noise	$f = 100\text{ kHz}$		20		nV/ $\sqrt{\text{Hz}}$
		$f = 1\text{ kHz}$		25		

5V Mid Power Mode Electrical Characteristics (Continued)

Unless otherwise specified, all limits are guaranteed for $T_J = 25^\circ\text{C}$, $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{\text{CM}} = V_O = V^+/2$, I_{SEL} pin connected to V^- through 100 k Ω resistor, $R_L = 100\text{ k}\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
i_n	Input-Referred Current Noise	$f = 1\text{ kHz}$		0.006		pA/ $\sqrt{\text{Hz}}$

5V Low Power Mode Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for $T_J = 25^\circ\text{C}$, $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{\text{CM}} = V_O = V^+/2$, I_{SEL} connected to V^- through 1 M Ω resistor, $R_L = 100\text{ k}\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
V_{OS}	Input Offset Voltage			± 1	± 4.5 ± 5	mV
ΔV_{OS}	Input Offset Voltage Difference	V_{OS} in Full Power Mode – V_{OS} in Low Power Mode		± 0.1	± 2	mV
TC V_{OS}	Input Offset Average Drift	(Note 8)		± 2		$\mu\text{V}/\text{C}$
I_B	Input Bias Current			50		fA
CMRR	Common Mode Rejection Ratio	V_{CM} Stepped from 0V to 3.5V	72 68	90		dB
PSRR	Power Supply Rejection Ratio	$V^+ = 2.7\text{V}$ to 5.5V	72 68	85		dB
CMVR	Input Common-Mode Voltage Range	CMRR $\geq 50\text{ dB}$	-0.3		3.8	V
A_{VOL}	Large Signal Voltage Gain	$V_O = 0.5\text{V}$ to 4.5V $R_L = 10\text{ k}\Omega$ $V_O = 0.5\text{V}$ to 4.5V $R_L = 100\text{ k}\Omega$		90 100 78		dB
V_O	Output Swing High	$R_L = 10\text{ k}\Omega$ $R_L = 100\text{ k}\Omega$		175 115	400 1600 200 230	mV from V^+
	Output Swing Low	$R_L = 10\text{ k}\Omega$ $R_L = 100\text{ k}\Omega$		250 150	1200 1800 165 180	mV
I_{SC}	Output Short Circuit Current	Sourcing, $V_O = 2.5\text{V}$ $V_{\text{ID}} = 100\text{ mV}$ Sinking, $V_O = 2.5\text{V}$ $V_{\text{ID}} = -100\text{ mV}$		-400 80 35	-100 -35	μA
I_S	Supply Current			5	7 8	μA
SR	Slew Rate (Note 7)	$A_V = +1$, $V_{\text{IN}} = 0.5\text{V}$ to 3.5V	10 8	28		V/ms
GBW	Gain Bandwidth Product	$C_L = 20\text{ pF}$		73		kHz
e_n	Input-Referred Voltage Noise	$f = 100\text{ kHz}$ $f = 1\text{ kHz}$		40 60		nV/ $\sqrt{\text{Hz}}$
i_n	Input-Referred Current Noise	$f = 1\text{ kHz}$		0.06		pA/ $\sqrt{\text{Hz}}$

Power Select Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for $T_J = 25^\circ\text{C}$, $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{CM} = V_O = V^+/2$, $R_L = 100\text{ k}\Omega$. **Bold-face** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
t_{LF}	Time from Low Power Mode to Full Power Mode			210		ns
t_{FL}	Time from Full Power Mode to Low Power Mode			500		ns
V_{REXT}	Voltage @ I_{SEL} Pin	I_{SEL} Pin Left Open	100	110	125	mV
R_{INT}			9	11	14.5	k Ω

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics Tables.

Note 2: Human Body Model is 1.5 k Ω in series with 100 pF. Machine Model is 0 Ω in series with 200 pF.

Note 3: Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150 $^\circ\text{C}$.

Note 4: The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PC board.

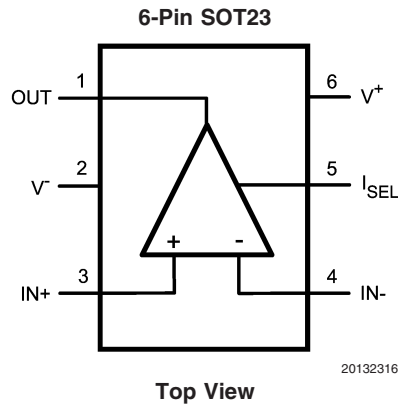
Note 5: Typical values represent the most likely parametric norm.

Note 6: All limits are guaranteed by testing or statistical analysis.

Note 7: Slew rate is the slower of the rising or falling slew rates.

Note 8: Offset voltage average drift is determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.

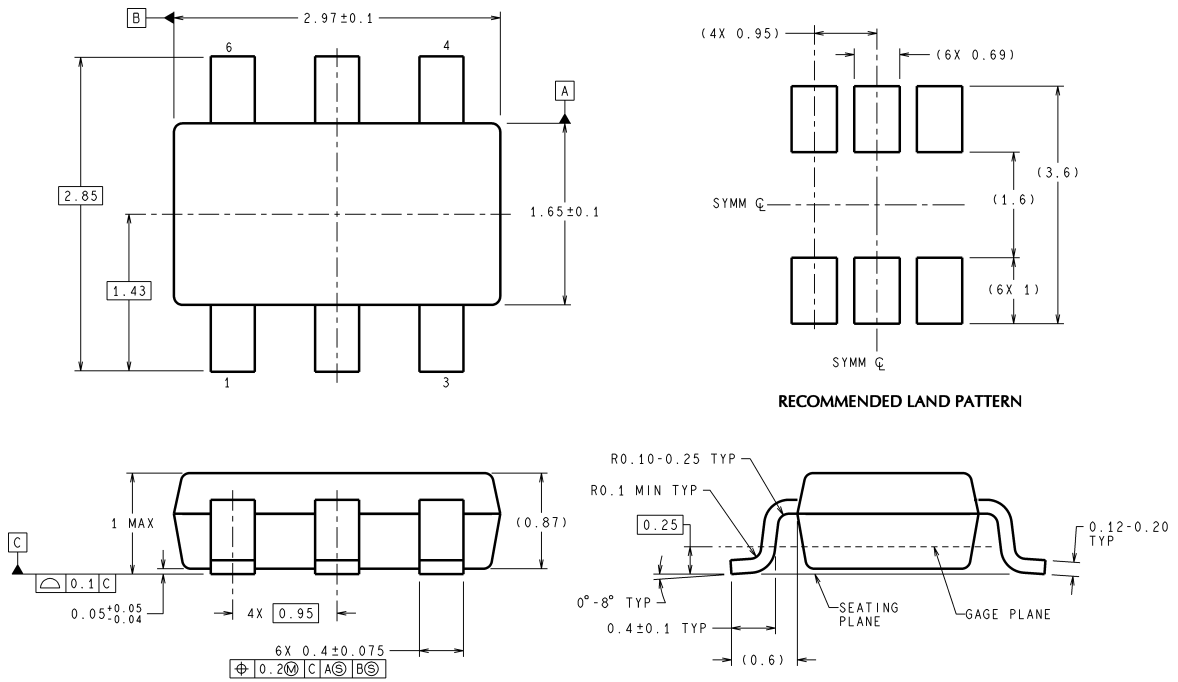
Connection Diagram



Ordering Information

Package	Part Number	Package Marking	Transport Media	NSC Drawing
6-Pin SOT23	LPV531MK	AV2A	1k Units Tape and Reel	MK06A
	LPV531MKX		3k Units Tape and Reel	

Physical Dimensions inches (millimeters) unless otherwise noted



DIMENSIONS ARE IN MILLIMETERS
6-Pin SOT23
NS Package Number MK06A

MK06A (Rev D)

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